

EF51J

ULTRAFAST RECOVERY GLASS PASSIVATED RECTIFIER CHIPS

VOLTAGE: 640V

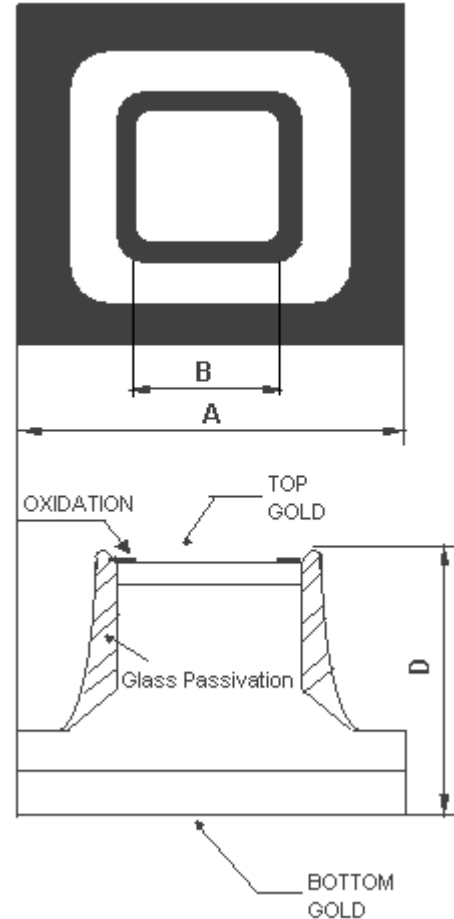
GPP DICE: 51MIL



FEATURE

Ultrafast Recovery Times
150°C Operating Junction Temperature
Low Forward Voltage
Low Leakage Current
Glass Passivated Junction
High surge capability

GPP 51MIL



A(mm)	B(mm)	D(mm)
1.27±0.03	0.66±0.03	0.31±0.02

	SYMBOL	EF51J	units
Maximum Recurrent Peak Reverse Voltage	V _{rrm}	640	V
Maximum RMS Voltage	V _{rms}	448	V
Maximum DC blocking Voltage	V _{dc}	640	V
Peak Forward Surge Current 8.3ms single half sine-wave superimposed on rated load	I _{fsm}	30	A
Maximum Forward Voltage at rated Forward Current and 25°C	V _f	1.65	at=1.0A V
Maximum DC Reverse Current Ta =25°C	I _r	5	μA
at rated DC blocking voltage Ta =125°C		50	μA
Maximum Reverse Recovery Time (Note 1)	T _{rr}	34	nS
Storage and Operating Temperature Range	T _{stg} , T _j	-55 to +150	°C

Note:
Reverse Recovery Condition I_f =0.5A, I_r =1.0A, I_{rr} =0.25A